



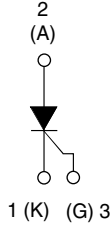
40TPS...APbF/40TPS...PbF High Voltage Series

Vishay High Power Products

Phase Control SCR, 35 A



TO-247AC



DESCRIPTION/FEATURES

The 40TPS...APbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature. Low Igt parts available.



RoHS* COMPLIANT

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level and lead (Pb)-free ("PbF" suffix).

PRODUCT SUMMARY

V_T at 40 A	< 1.45 V
I_{TSM}	500 A
V_{RRM}	800/1200 V

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	35	A
I_{RMS}		55	
V_{RRM}/V_{DRM}		800/1200	V
I_{TSM}		500	A
V_T	40 A, $T_J = 25\text{ }^\circ\text{C}$	1.45	V
dV/dt		1000	V/ μs
dI/dt		100	A/ μs
T_J		- 40 to 125	$^\circ\text{C}$

VOLTAGE RATINGS

PART NUMBER	V_{RRM}/V_{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
40TPS08APbF	800	900	10
40TPS12APbF	1200	1300	
40TPS08PbF	800	900	
40TPS12PbF	1200	1300	

* Pb containing terminations are not RoHS compliant, exemptions may apply

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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	$I_{T(AV)}$	$T_C = 79\text{ }^\circ\text{C}$, 180° conduction half sine wave		35	A
Maximum continuous RMS on-state current as AC switch	$I_{T(RMS)}$			55	
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	Initial $T_J = T_J$ maximum	500	
		10 ms sine pulse, no voltage reapplied		600	
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied		1250	A^2s
		10 ms sine pulse, no voltage reapplied		1760	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1$ to 10 ms, no voltage reapplied		12 500	$A^2\sqrt{s}$
Low level value of threshold voltage	$V_{T(TO)1}$	$T_J = 125\text{ }^\circ\text{C}$		1.02	V
High level value of threshold voltage	$V_{T(TO)2}$			1.23	
Low level value of on-state slope resistance	$r_{\theta 1}$			9.74	$m\Omega$
High level value of on-state slope resistance	$r_{\theta 2}$			7.50	
Maximum peak on-state voltage	V_{TM}	110 A, $T_J = 25\text{ }^\circ\text{C}$		1.85	V
Maximum rate of rise of turned-on current	di/dt	$T_J = 25\text{ }^\circ\text{C}$		100	$A/\mu s$
Maximum holding current	I_H			150	mA
Maximum latching current	I_L			300	
Maximum reverse and direct leakage current	I_{RRM}/I_{DRM}	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	0.5	
		$T_J = 125\text{ }^\circ\text{C}$		10	
Maximum rate of rise of off-state voltage 40TPS08	dV/dt	$T_J = T_J$ maximum, linear to 80 % V_{DRM} , $R_g-k = \text{Open}$		500	$V/\mu s$
Maximum rate of rise of off-state voltage 40TPS12				1000	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P_{GM}			10	W
Maximum average gate power	$P_{G(AV)}$			2.5	
Maximum peak gate current	I_{GM}			2.5	A
Maximum peak negative gate voltage	$-V_{GM}$			10	V
Maximum required DC gate voltage to trigger	V_{GT}	$T_J = -40\text{ }^\circ\text{C}$	Anode supply = 6 V resistive load	4.0	V
		$T_J = 25\text{ }^\circ\text{C}$		2.5	
		$T_J = 125\text{ }^\circ\text{C}$		1.7	
Maximum required DC gate current to trigger	I_{GT}	$T_J = -40\text{ }^\circ\text{C}$		270	mA
		$T_J = 25\text{ }^\circ\text{C}$		150	
		$T_J = 125\text{ }^\circ\text{C}$		80	
		$T_J = 25\text{ }^\circ\text{C}$, for 40TPS08APbF and 40TPS12APbF		40	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^\circ\text{C}$, $V_{DRM} = \text{Rated value}$		0.25	V
Maximum DC gate current not to trigger	I_{GD}			6	mA



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THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.6	°C/W
Maximum thermal resistance, junction to ambient	R_{thJA}		40	
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased	0.2	
Approximate weight			6	g
			0.21	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style TO-247AC	40TPS08A	
			40TPS12A	
			40TPS08	
			40TPS12	

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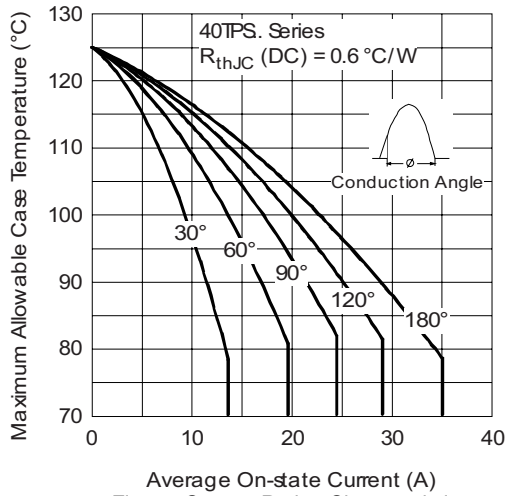


Fig. 1 - Current Rating Characteristics

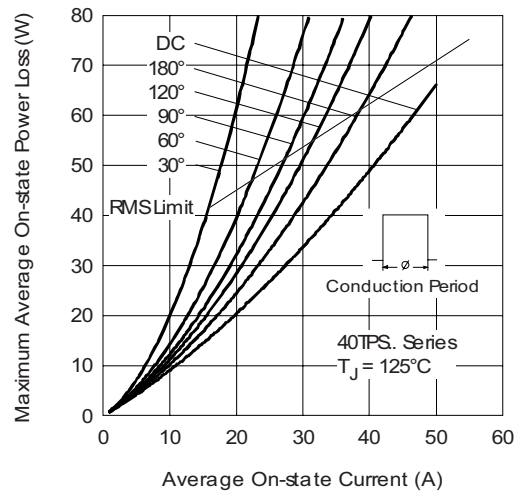


Fig. 4 - On-State Power Loss Characteristics

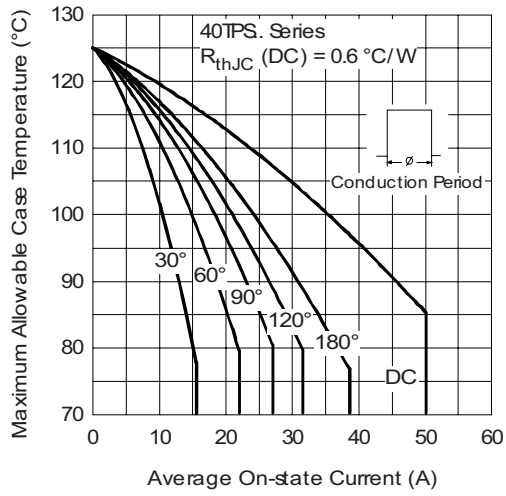


Fig. 2 - Current Rating Characteristics

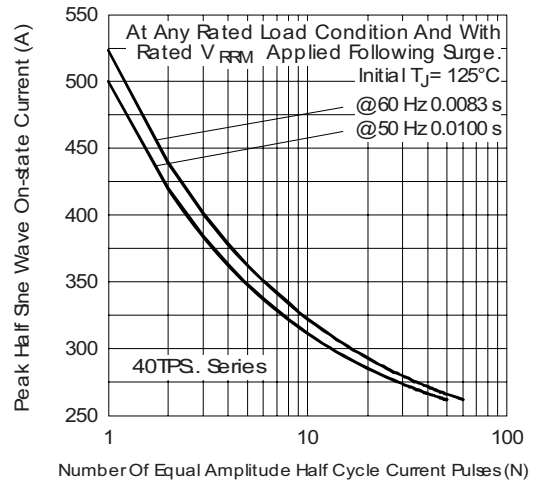


Fig. 5 - Maximum Non-Repetitive Surge Current

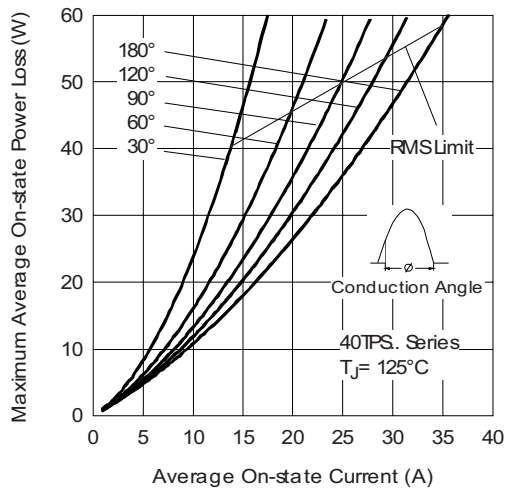


Fig. 3 - On-State Power Loss Characteristics

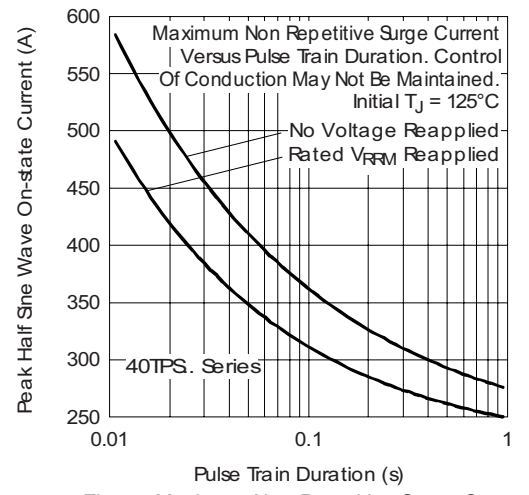


Fig. 6 - Maximum Non-Repetitive Surge Current



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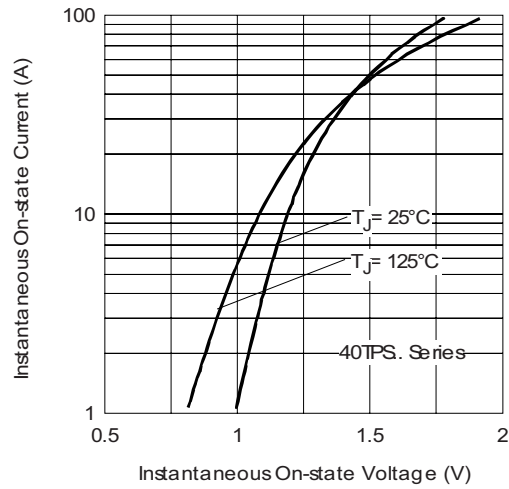


Fig. 7 - On-State Voltage Drop Characteristics

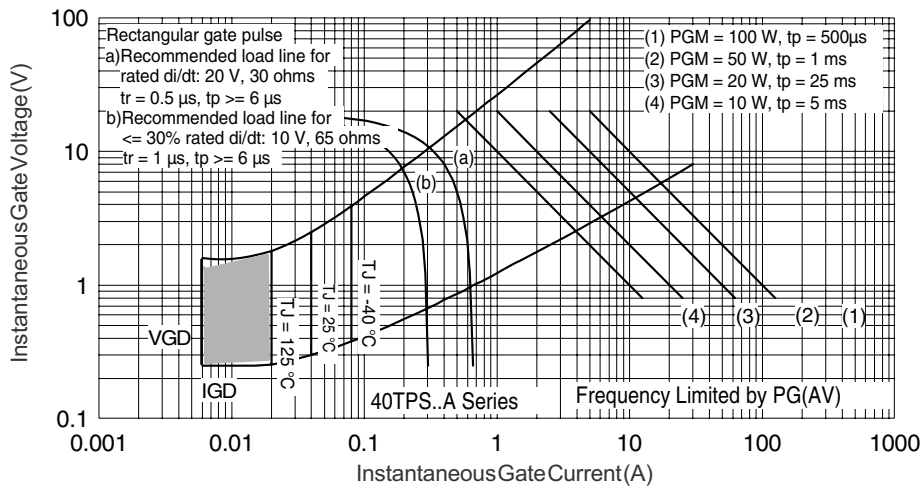


Fig. 8 - Gate Characteristics

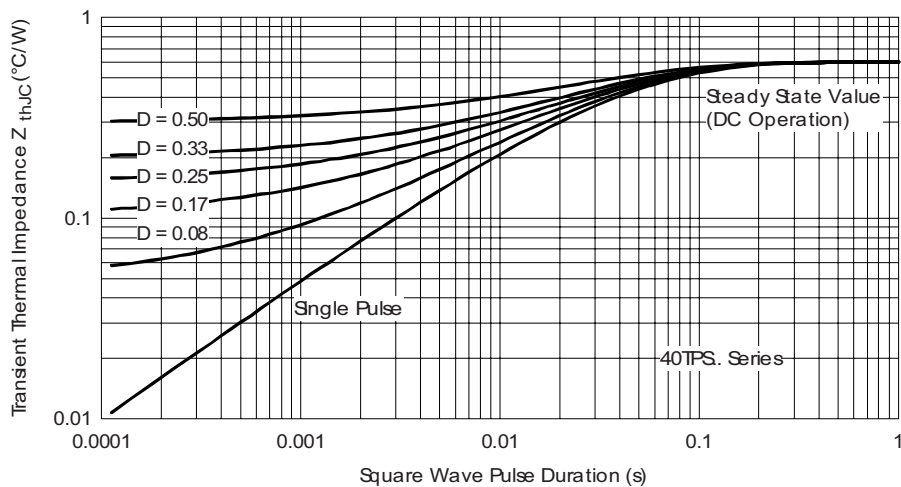


Fig. 9 - Thermal Impedance Z_{thjC} Characteristics

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ORDERING INFORMATION TABLE

Device code	40	T	P	S	12	A	PbF
	①	②	③	④	⑤	⑥	⑦
①	-	Current rating (40 = 40 A)					
②	-	Circuit configuration: T = Thyristor					
③	-	Package: P = TO-247					
④	-	Type of silicon: S = Standard recovery rectifier					
⑤	-	Voltage ratings					08 = 800 V 12 = 1200 V
⑥	-	<ul style="list-style-type: none">• A = Low Igt selection 40 mA maximum• None = Standard Igt selection					
⑦	-	<ul style="list-style-type: none">• None = Standard production• PbF = Lead (Pb)-free					

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95223
Part marking information	http://www.vishay.com/doc?95226



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